

WHAT IS CLAIMED IS:

1. A semiconductor wafer comprising first and second semiconductor wafers having crystal orientation display sections to be nicks indicative of crystal orientations formed on fringes thereof,

wherein said crystal orientation display sections are indicative of an identical crystal orientation in said first and second semiconductor wafers, and

said first and second semiconductor wafers are bonded with said crystal orientation display sections shifted from each other.

2. The semiconductor wafer according to claim 1, wherein both of said first and second semiconductor wafers are (100) wafers in which (100) planes are main surfaces, and

said crystal orientation display sections are shifted from each other by 45 degrees or 135 degrees.

3. The semiconductor wafer according to claim 2, wherein said first semiconductor wafer is a wafer for a support substrate and said second semiconductor wafer is a wafer for a device formation, and

a main surface of said wafer for the device formation is provided with a semiconductor device including a MOS transistor in which a channel direction between a source and a drain is parallel with a direction of a crystal orientation $\langle 100 \rangle$.

4. The semiconductor wafer according to claim 1, wherein said first semiconductor wafer is a wafer for a support substrate,

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an insulating film is formed on a main surface of at least one of said wafer for

the support substrate and said wafer for the SOI layer.

8. A semiconductor wafer comprising first and second semiconductor wafers having bulk structures,

wherein said first and second semiconductor wafers are bonded with crystal orientations shifted from each other.

9. The semiconductor wafer according to claim 8, wherein both of said first and second semiconductor wafers are (100) wafers in which (100) planes are main surfaces, and

said crystal orientations are shifted from each other by 45 degrees or 135 degrees.

10. The semiconductor wafer according to claim 9, wherein said first semiconductor wafer is a wafer for a support substrate and said second semiconductor wafer is a wafer for a device formation, and

a main surface of said wafer for the device formation is provided with a semiconductor device including a MOS transistor in which a channel direction between a source and a drain is parallel with a direction of a crystal orientation $\langle 100 \rangle$.